MOSFET - POWER, Dual, Complementary, TSOP-6

30 V, +2.9/-2.2 A

NTGD4167C

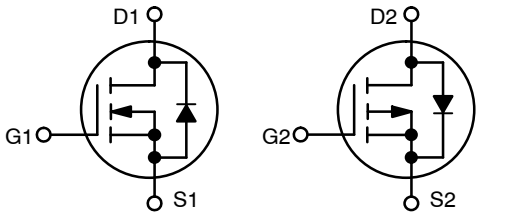
$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX (Note 1)
N-Ch 30 V	90 mΩ @ 4.5 V	2.6 A
	125 mΩ @ 2.5 V	2.2 A
P-Ch −30 V	170 mΩ @ −4.5 V	−1.9 A
	300 mΩ @ −2.5 V	−1.0 A

Features

- Complementary N-Channel and P-Channel MOSFET
- Small Size (3 x 3 mm) Dual TSOP-6 Package
- Leading Edge Trench Technology for Low On Resistance
- Reduced Gate Charge to Improve Switching Response
- Independently Connected Devices to Provide Design Flexibility
- This is a Pb-Free Device

Applications

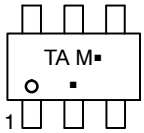
- DC-DC Conversion Circuits
- Load/Power Switching with Level Shift



N−CHANNEL MOSFET P−CHANNEL MOSFET

TSOP-6
CASE 318G
STYLE 13

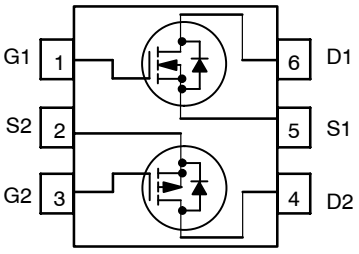
MARKING DIAGRAM



TA = Specific Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

PIN CONNECTION



(Top View)

ORDERING INFORMATION

See detailed ordering and shipping information in on page 9 of this data sheet.

MAXIMUM RATINGS (T_J = 25 °C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	30	V
Gate-to-Source Voltage (N-Ch & P-Ch)			V_{GS}	±12	V
N-Channel Continuous Drain Current (Note 1)	Steady State	T_A = 25 °C	I_D	2.6	A
		T_A = 85 °C		1.9	
	t ≤ 5 s	T_A = 25 °C		2.9	
P-Channel Continuous Drain Current (Note 1)	Steady State	T_A = 25 °C	I_D	−1.9	A
		T_A = 85 °C		−1.4	
	t ≤ 5 s	T_A = 25 °C		−2.2	
Power Dissipation (Note 1)	Steady State	T_A = 25 °C	P_D	0.9	W
	t ≤ 5 s			1.1	
Pulsed Drain Current	N-Ch	t_p = 10 μs	I_{DM}	8.6	A
	P-Ch			−6.3	
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	°C
Source Current (Body Diode)			I_S	±0.9	A
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)			T_L	260	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	140	°C/W
Junction-to-Ambient – t ≤ 5 s (Note 1)	$R_{\theta JA}$	110	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

ELECTRICAL CHARACTERISTICS (T_J = 25 °C unless otherwise noted)

Parameter	Symbol	N/P	Test Conditions		Min	Typ	Max	Unit
OFF CHARACTERISTICS								
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	N	V_{GS} = 0 V	I_D = 250 μA	30			V
		P		I_D = −250 μA	−30			
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	N				21.4		mV/°C
		P				22.2		
Zero Gate Voltage Drain Current	I_{DSS}	N	V_{GS} = 0 V, V_{DS} = 24 V	T_J = 25 °C			1.0	μA
		P	V_{GS} = 0 V, V_{DS} = −24 V				−1.0	
		N	V_{GS} = 0 V, V_{DS} = 24 V	T_J = 85 °C			10	
		P	V_{GS} = 0 V, V_{DS} = −24 V				−10	
Gate-to-Source Leakage Current	I_{GSS}	N	V_{DS} = 0 V, V_{GS} = ±12 V				±100	nA
		P	V_{DS} = 0 V, V_{GS} = ±12 V				±100	
ON CHARACTERISTICS (Note 2)								
Gate Threshold Voltage	$V_{GS(TH)}$	N	V_{GS} = V_{DS}	I_D = 250 μA	0.5	0.9	1.5	V
		P		I_D = −250 μA	−0.5	−1.1	−1.5	
Drain-to-Source On Resistance	$R_{DS(on)}$	N	V_{GS} = 4.5 V , I_D = 2.6 A			52	90	mΩ
			V_{GS} = 2.5 V , I_D = 2.2 A			67	125	
		P	V_{GS} = −4.5 V , I_D = −1.9 A			130	170	
			V_{GS} = −2.5 V, I_D = −1.0 A			202	300	
Forward Transconductance	g_{FS}	N	V_{DS} = 15 V, I_D = 2.6 A			2.6		S
		P	V_{DS} = −15 V , I_D = −1.9 A			2.6		
CHARGES AND CAPACITANCES								
Input Capacitance	C_{ISS}	N	f = 1 MHz, V_{GS} = 0 V	V_{DS} = 15 V		295		pF
Output Capacitance	C_{OSS}					48		
Reverse Transfer Capacitance	C_{RSS}					27		
Input Capacitance	C_{ISS}	P		V_{DS} = −15 V		419		
Output Capacitance	C_{OSS}					51		
Reverse Transfer Capacitance	C_{RSS}					26		
Total Gate Charge	$Q_{G(TOT)}$	N	V_{GS} = 4.5 V, V_{DS} = 15 V, I_D = 2.0 A			3.7	5.5	nC
Threshold Gate Charge	$Q_{G(TH)}$					0.6		
Gate-to-Source Gate Charge	Q_{GS}					0.9		
Gate-to-Drain “Miller” Charge	Q_{GD}					0.8		
Total Gate Charge	$Q_{G(TOT)}$	P	V_{GS} = −4.5 V, V_{DS} = −15 V, I_D = −2.0 A			3.9	6.0	
Threshold Gate Charge	$Q_{G(TH)}$					0.6		
Gate-to-Source Gate Charge	Q_{GS}					1.0		
Gate-to-Drain “Miller” Charge	Q_{GD}					1.0		

ELECTRICAL CHARACTERISTICS (T_J = 25 °C unless otherwise noted)

Parameter	Symbol	N/P	Test Conditions	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS (Note 3)							
Turn-On Delay Time	$t_{d(ON)}$	N	V_{GS} = 4.5 V, V_{DD} = 15 V, I_D = 1.0 A, R_G = 6.0 Ω		7.0		ns
Rise Time	t_r				4.0		
Turn-Off Delay Time	$t_{d(OFF)}$				14		
Fall Time	t_f				2.0		
Turn-On Delay Time	$t_{d(ON)}$	P	V_{GS} = −4.5 V, V_{DD} = −15 V, I_D = −1.0 A, R_G = 6.0 Ω		8.0		
Rise Time	t_r				8.0		
Turn-Off Delay Time	$t_{d(OFF)}$				22		
Fall Time	t_f				8.0		

2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
3. Switching characteristics are independent of operating junction temperatures.

ELECTRICAL CHARACTERISTICS (T_J = 25 °C unless otherwise noted)

Parameter	Symbol	N/P	Test Conditions		Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS								
Forward Diode Voltage	V_{SD}	N	V_{GS} = 0 V, T_J = 25 °C	I_S = 0.9 A		0.7	1.2	V
		P		I_S = −0.9 A		−0.8	−1.2	
Reverse Recovery Time	t_{RR}	N	V_{GS} = 0 V, dI_S / dt = 100 A/μs, I_S = 0.9 A			8.0		ns
Charge Time	t_a					5.0		
Discharge Time	t_b					3.0		
Reverse Recovery Charge	Q_{RR}					3.0		nC
Reverse Recovery Time	t_{RR}	P	V_{GS} = 0 V, dI_S / dt = 100 A/μs, I_S = −0.9 A			12		ns
Charge Time	t_a					10		
Discharge Time	t_b					2.0		
Reverse Recovery Charge	Q_{RR}					7.0		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

N-CHANNEL TYPICAL CHARACTERISTICS

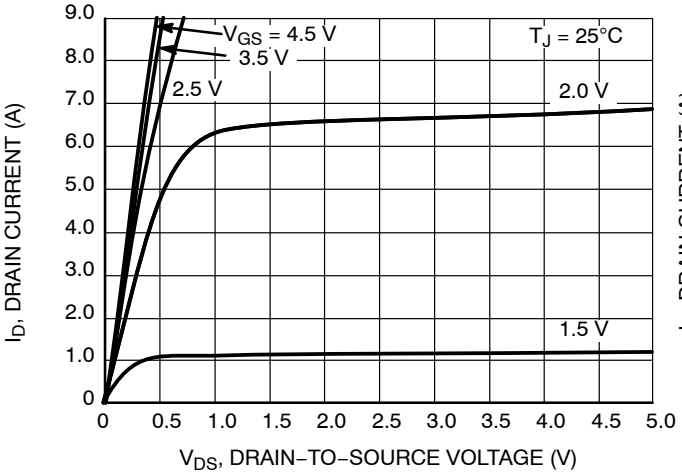


Figure 1. On−Region Characteristics

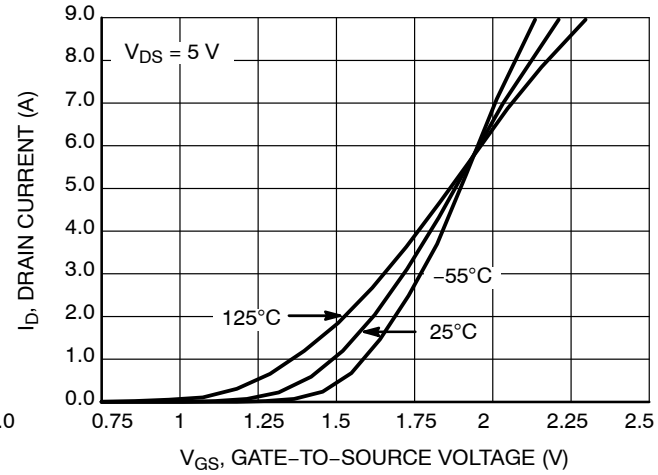


Figure 2. Transfer Characteristics

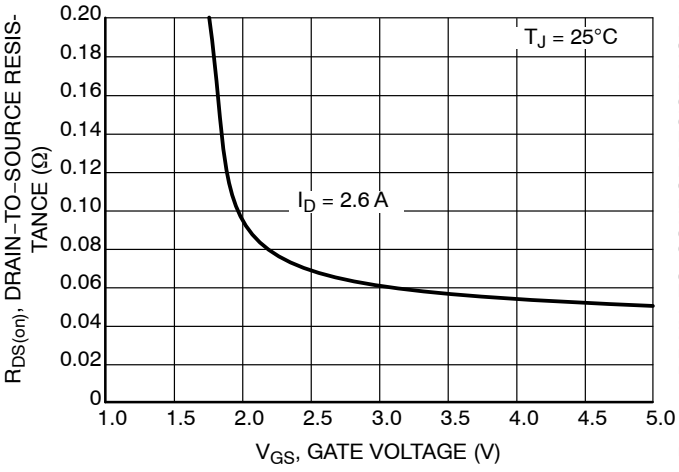


Figure 3. On−Region vs. Gate−To−Source Voltage

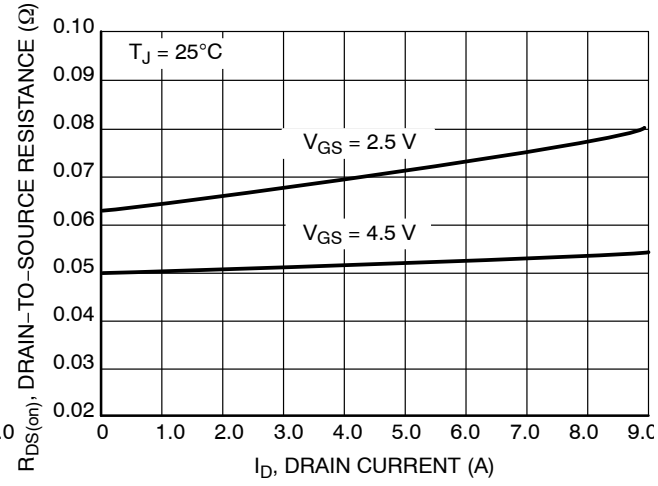


Figure 4. On−Resistance vs. Drain Current and Temperature

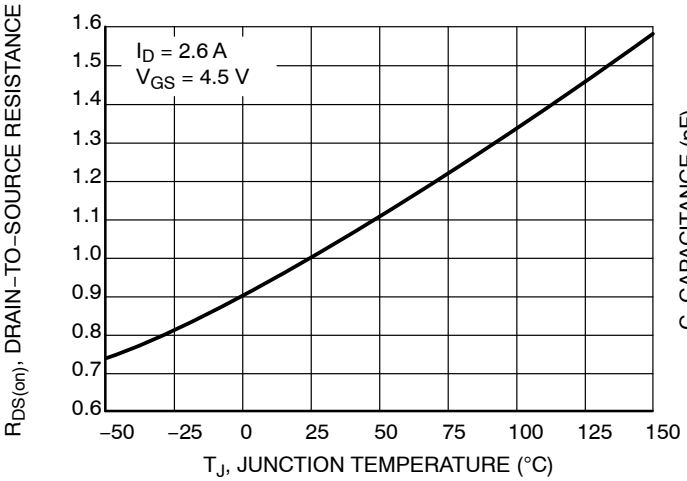


Figure 5. On−Resistance Variation with Temperature

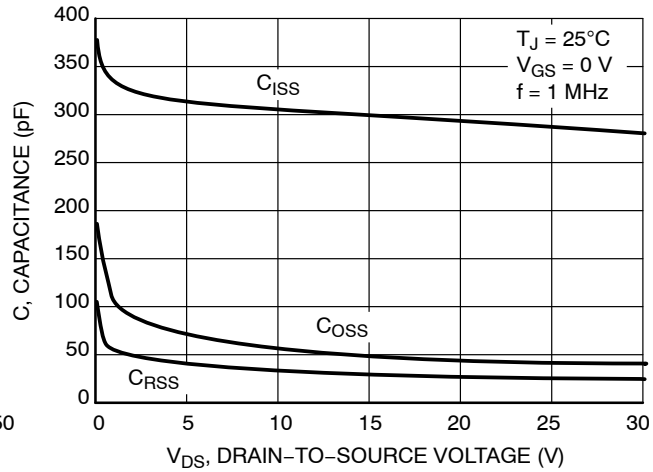


Figure 6. Capacitance Variation

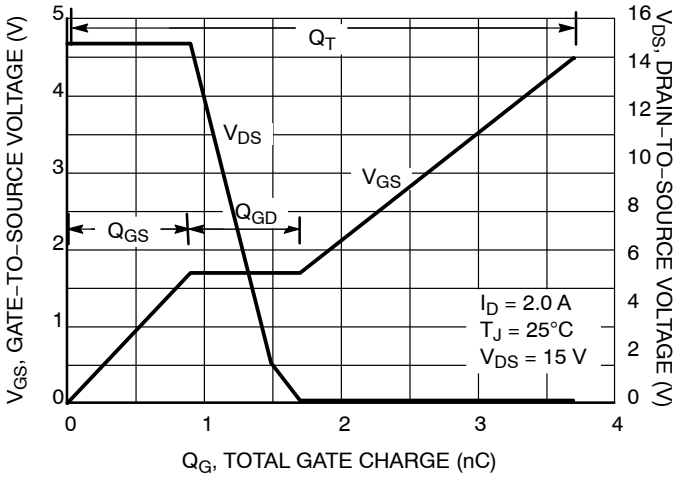


Figure 7. Gate−to−Source and Drain−to−Source Voltage versus Total Charge

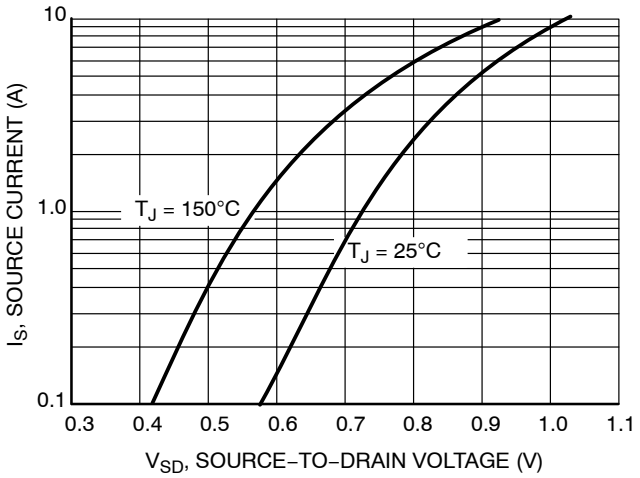


Figure 8. Diode Forward Voltage versus Current

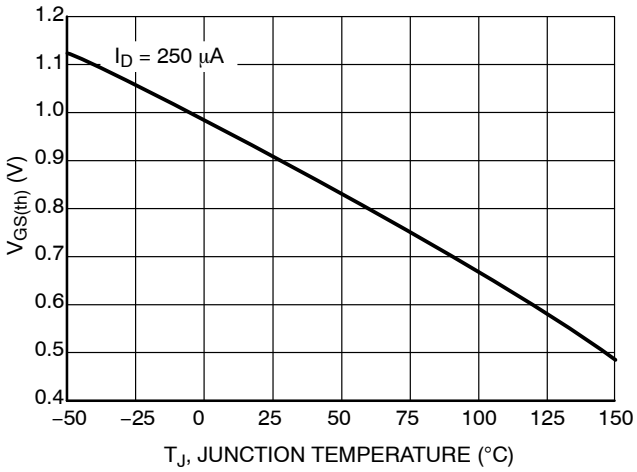


Figure 9. Threshold Voltage

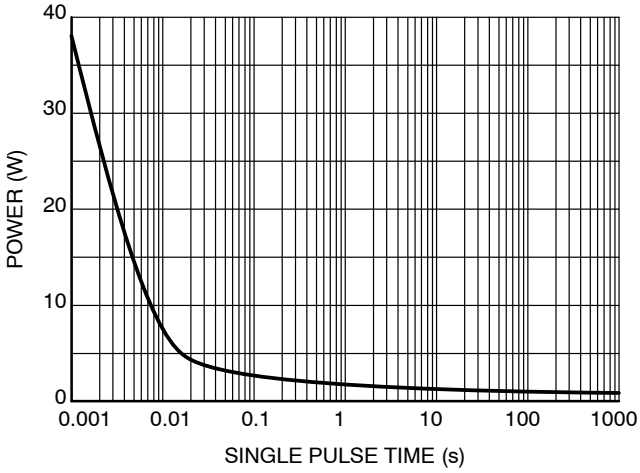


Figure 10. Single Pulse Maximum Power Dissipation

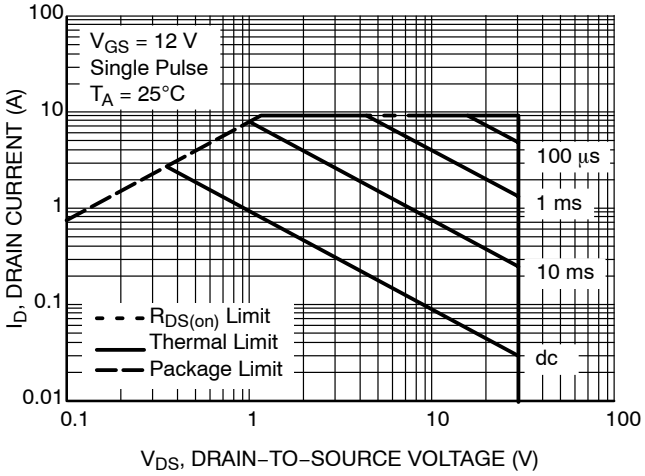


Figure 11. Maximum Rated Forward Biased Safe Operating Area

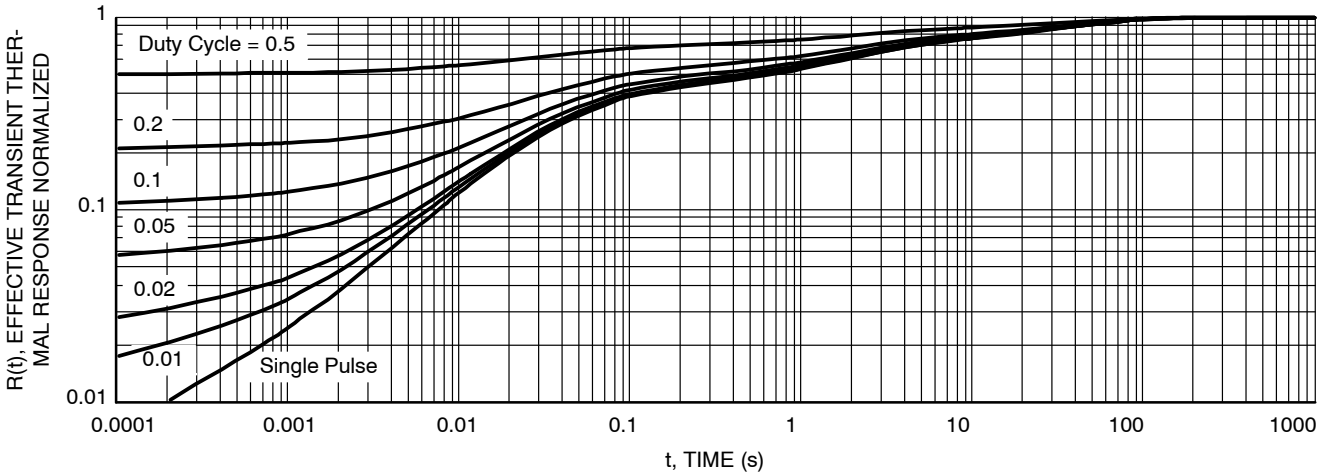


Figure 12. FET Thermal Response

P-CHANNEL TYPICAL CHARACTERISTICS

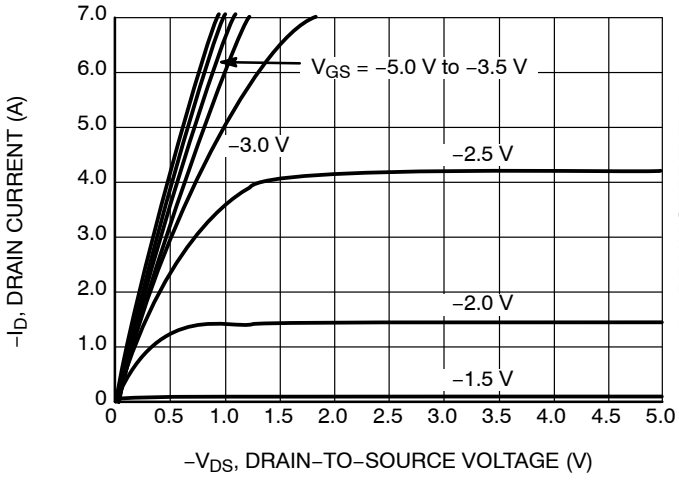


Figure 13. On−Region Characteristics

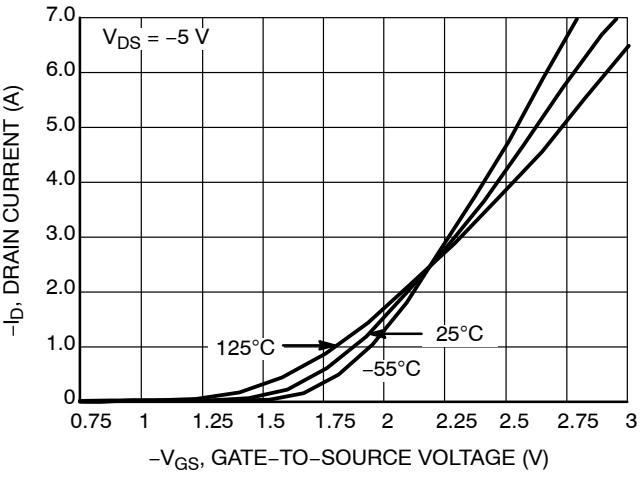


Figure 14. Transfer Characteristics

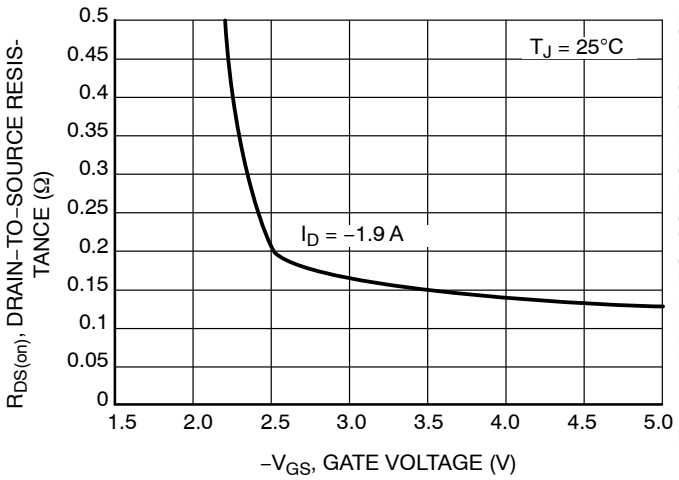


Figure 15. On−Region vs. Gate−To−Source Voltage

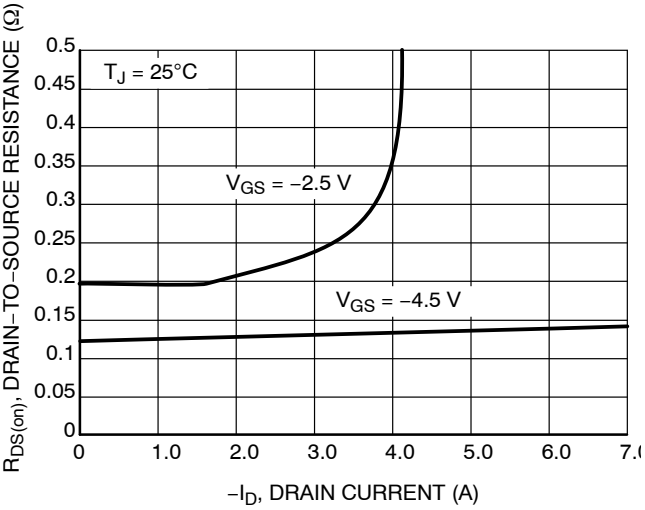


Figure 16. On−Resistance vs. Drain Current and Temperature

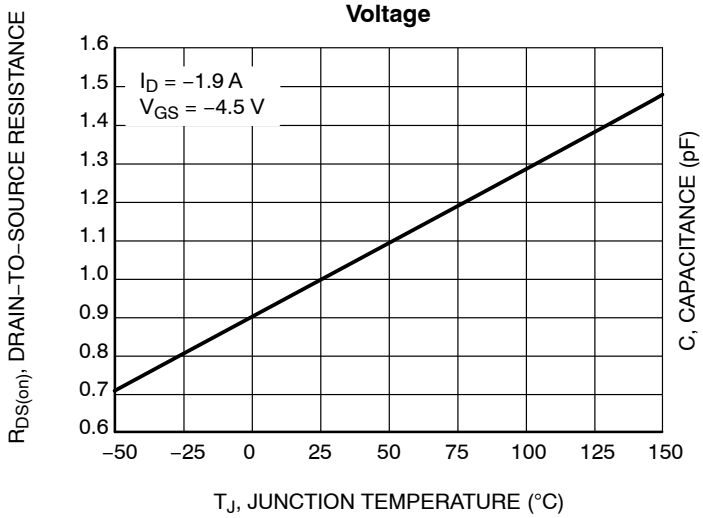


Figure 17. On−Resistance Variation with Temperature

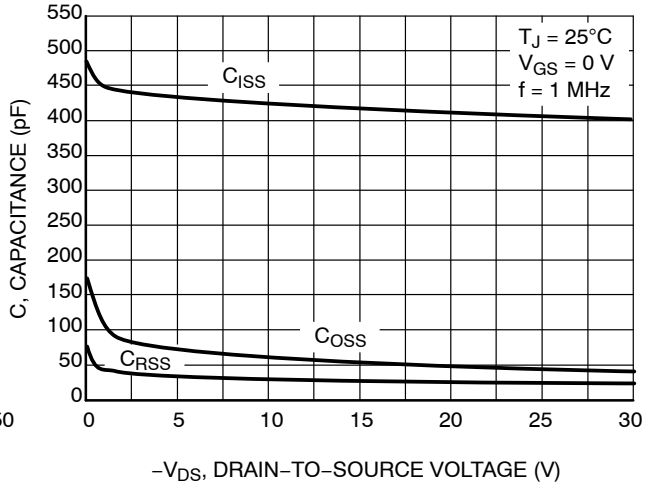


Figure 18. Capacitance Variation

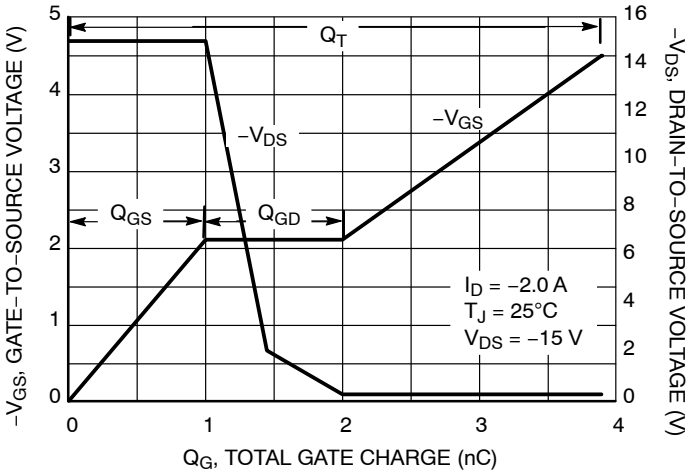


Figure 19. Gate−to−Source and Drain−to−Source Voltage versus Total Charge

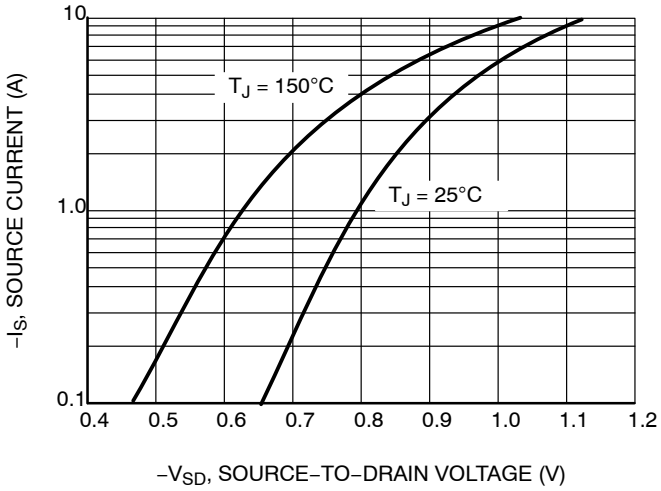


Figure 20. Diode Forward Voltage versus Current

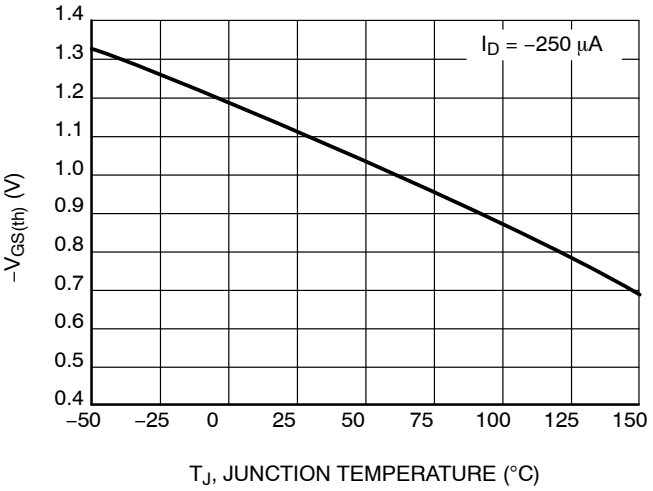


Figure 21. Threshold Voltage

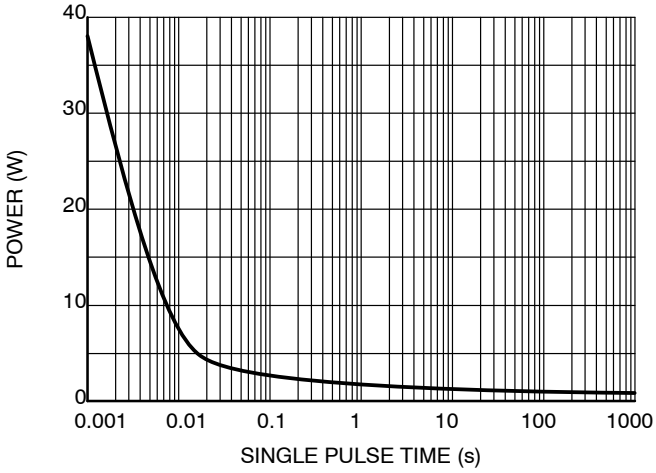


Figure 22. Single Pulse Maximum Power Dissipation

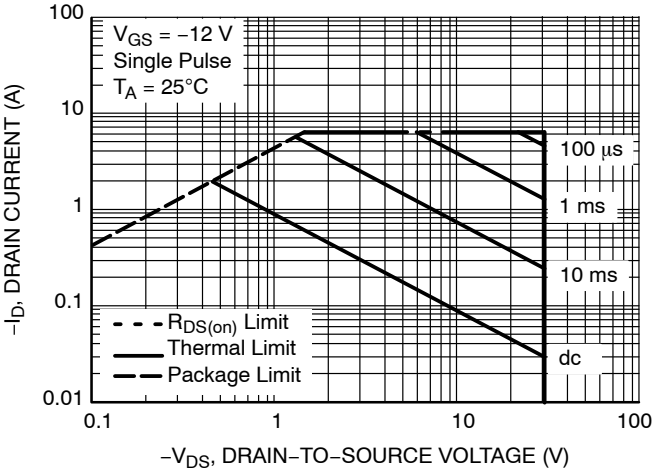


Figure 23. Maximum Rated Forward Biased Safe Operating Area

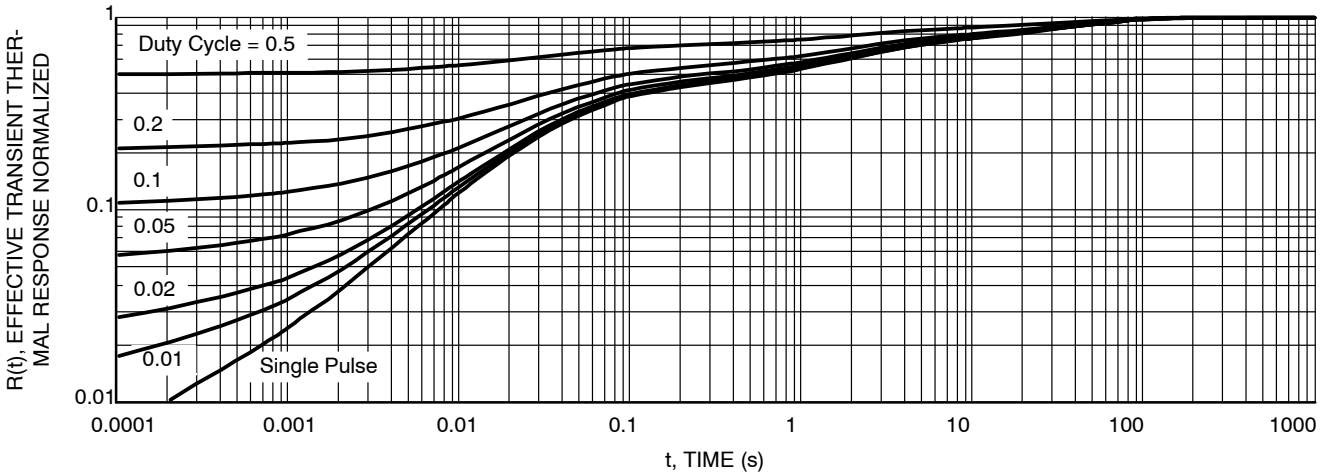
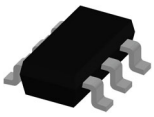


Figure 24. FET Thermal Response

ORDERING INFORMATION

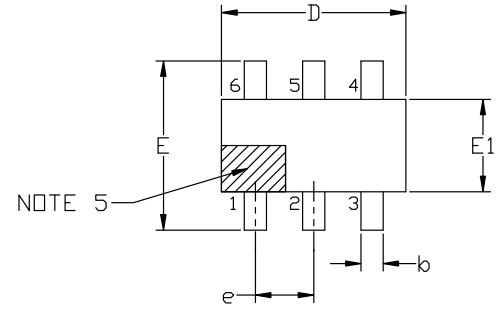
Device	Package	Shipping†
NTGD4167CT1G	TSOP6 (Pb-Free)	3000 / Tape & Reel

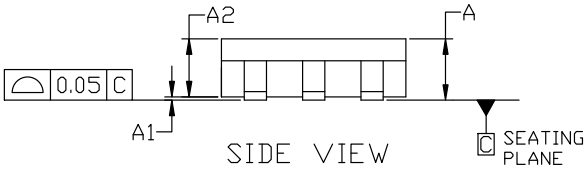
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

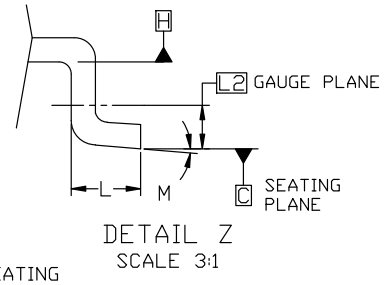


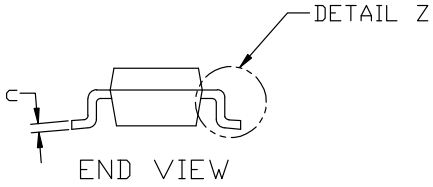
TSOP−6 3.00x1.50x0.90, 0.95P
CASE 318G
ISSUE W

DATE 26 FEB 2024



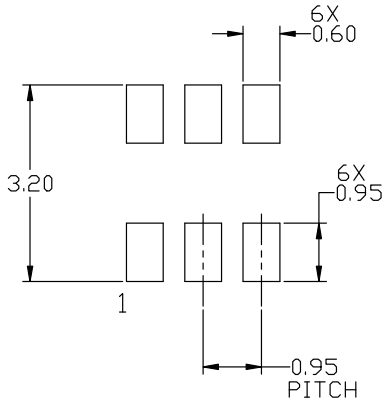






NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.
5. PIN 1 INDICATOR MUST BE LOCATED IN THE INDICATED ZONE

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.01	0.06	0.10
A2	0.80	0.90	1.00
b	0.25	0.38	0.50
c	0.10	0.18	0.26
D	2.90	3.00	3.10
E	2.50	2.75	3.00
E1	1.30	1.50	1.70
e	0.85	0.95	1.05
L	0.20	0.40	0.60
L2	0.25 BSC		
M	0°	---	10°



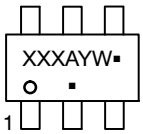
RECOMMENDED MOUNTING FOOTPRINT

*For additional information on our Pb-Free strategy and soldering details, please download th e ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.

TSOP−6 3.00x1.50x0.90, 0.95P
CASE 318G
ISSUE W

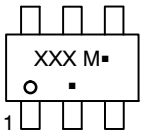
DATE 26 FEB 2024

GENERIC MARKING DIAGRAM*



IC

XXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb−Free Package



STANDARD

XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 2:
PIN 1. EMITTER 2
2. BASE 1
3. COLLECTOR 1
4. EMITTER 1
5. BASE 2
6. COLLECTOR 2

STYLE 3:
PIN 1. ENABLE
2. N/C
3. R BOOST
4. Vz
5. V in
6. V out

STYLE 4:
PIN 1. N/C
2. V in
3. NOT USED
4. GROUND
5. ENABLE
6. LOAD

STYLE 5:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

STYLE 6:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 7:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. N/C
5. COLLECTOR
6. EMITTER

STYLE 8:
PIN 1. Vbus
2. D(in)
3. D(in)+
4. D(out)+
5. D(out)
6. GND

STYLE 9:
PIN 1. LOW VOLTAGE GATE
2. DRAIN
3. SOURCE
4. DRAIN
5. DRAIN
6. HIGH VOLTAGE GATE

STYLE 10:
PIN 1. D(OUT)+
2. GND
3. D(OUT)−
4. D(IN)−
5. VBUS
6. D(IN)+

STYLE 11:
PIN 1. SOURCE 1
2. DRAIN 2
3. DRAIN 2
4. SOURCE 2
5. GATE 1
6. DRAIN 1/GATE 2

STYLE 12:
PIN 1. I/O
2. GROUND
3. I/O
4. I/O
5. VCC
6. I/O

STYLE 13:
PIN 1. GATE 1
2. SOURCE 2
3. GATE 2
4. DRAIN 2
5. SOURCE 1
6. DRAIN 1

STYLE 14:
PIN 1. ANODE
2. SOURCE
3. GATE
4. CATHODE/DRAIN
5. CATHODE/DRAIN
6. CATHODE/DRAIN

STYLE 15:
PIN 1. ANODE
2. SOURCE
3. GATE
4. DRAIN
5. N/C
6. CATHODE

STYLE 16:
PIN 1. ANODE/CATHODE
2. BASE
3. EMITTER
4. COLLECTOR
5. ANODE
6. CATHODE

STYLE 17:
PIN 1. EMITTER
2. BASE
3. ANODE/CATHODE
4. ANODE
5. CATHODE
6. COLLECTOR

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales